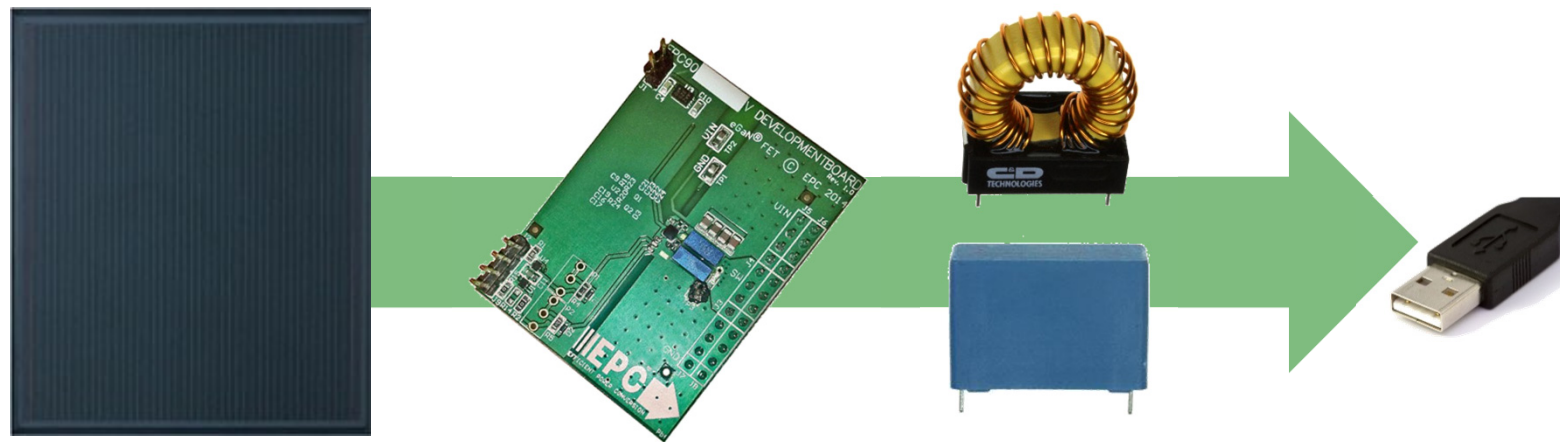
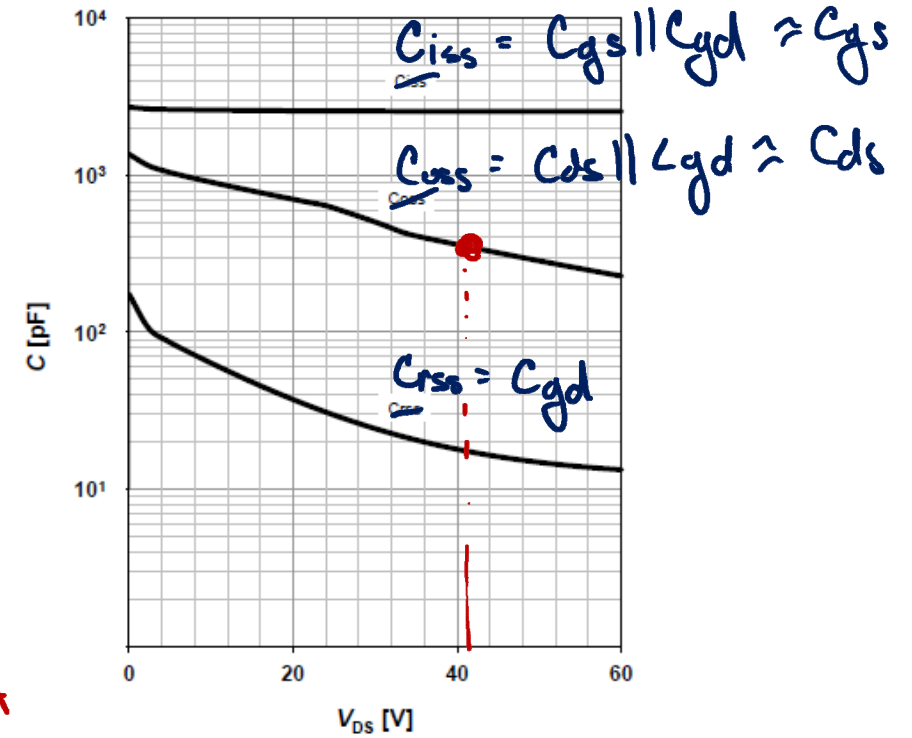
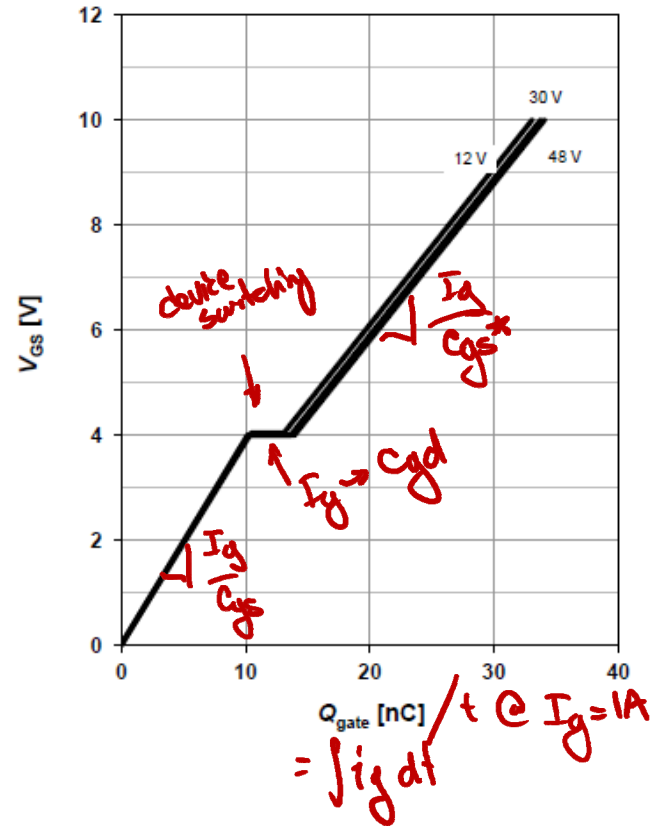
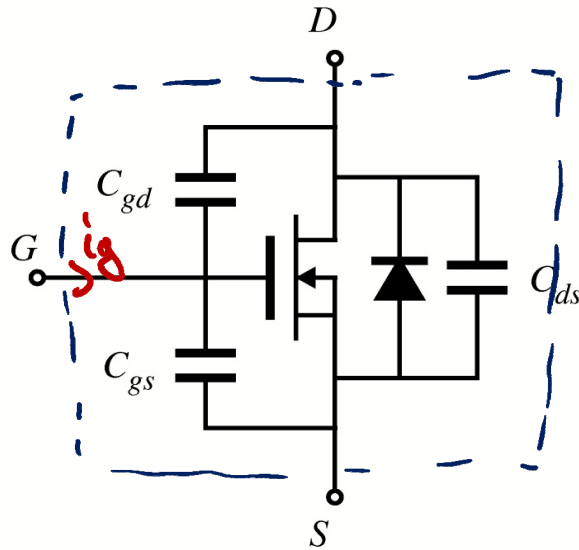


Announcements

- Experiment 1 assigned
 - Model PV panel for future converter design/analysis
 - Self-assign lab groups of 3 in canvas **this week**
 - Complete experiment next week 9/23-9/27
 - Report due 10/4



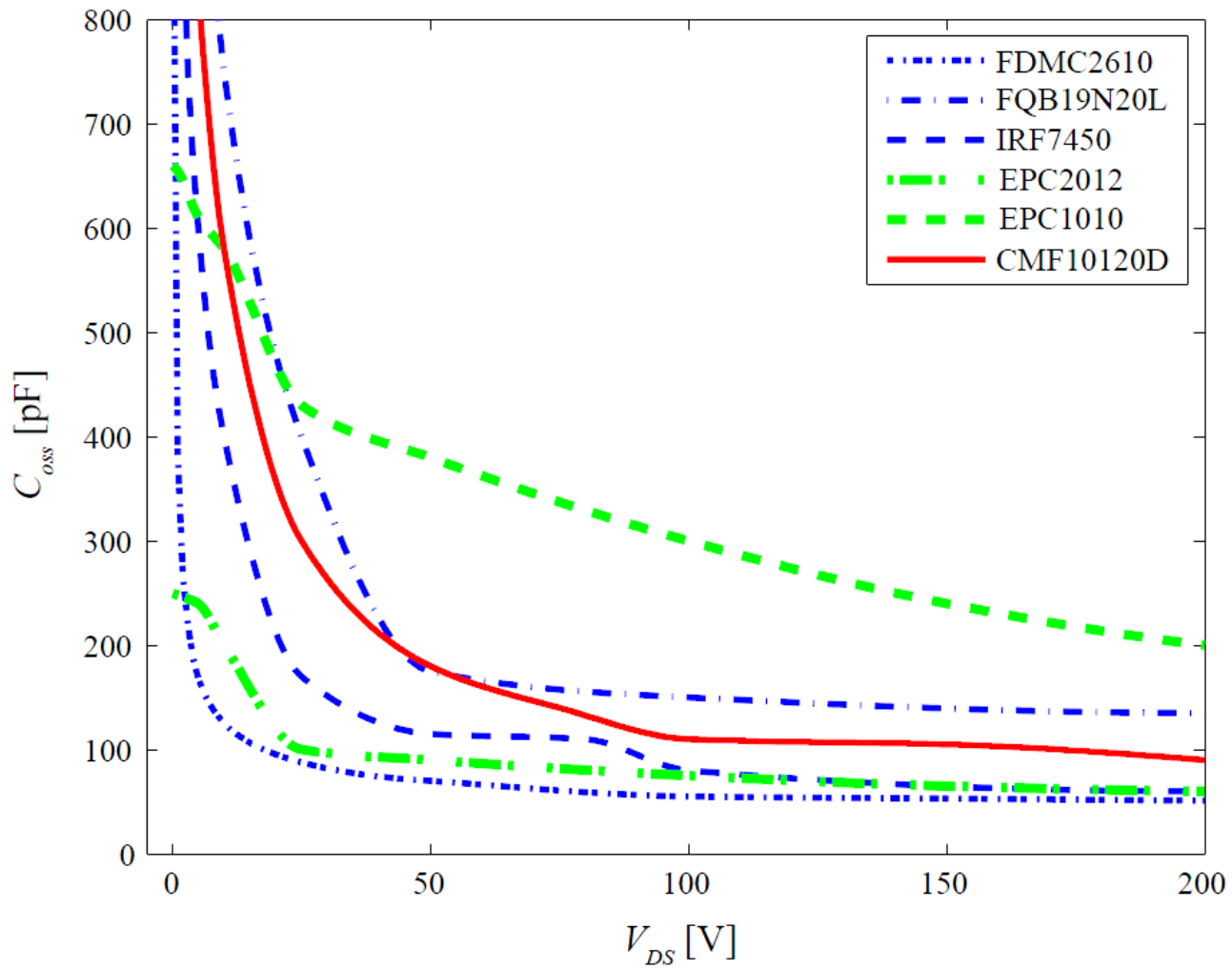
MOSFET Equivalent Circuit



"overlap loss" during time
 to get from $V_{gs} = V_{th}$
 to $V_{gs} = V_{gs,max}$

↳ analysis w/
 nonlinear caps
 ECE 581

Example C_{oss} Curves



$$C_{ds}(V_{ds}) \approx \frac{C_0}{\sqrt{1 + \left(\frac{V_{ds}}{V_0}\right)^m}}$$

Device Figures-of-Merit

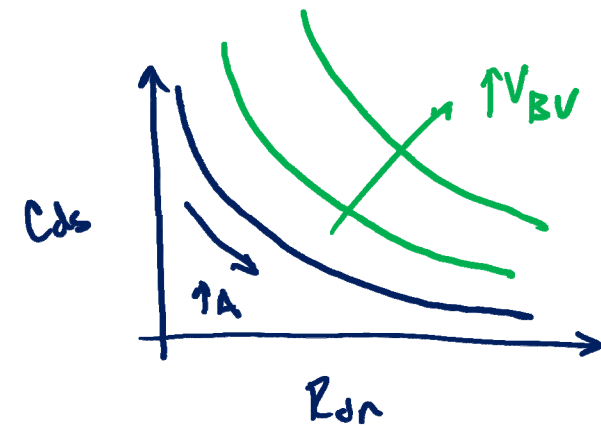
for a given material: set n_D in n^- material & height of drift region so that we hit designed V_{BV} @ E_{crit}
 model only drift region resistance

$$R_{sp} = R_{on} \cdot A = \frac{4V_{BV}^2}{\mu_n E_{crit}^3} \rightarrow \text{"Baliga's Figure of Merit"}$$

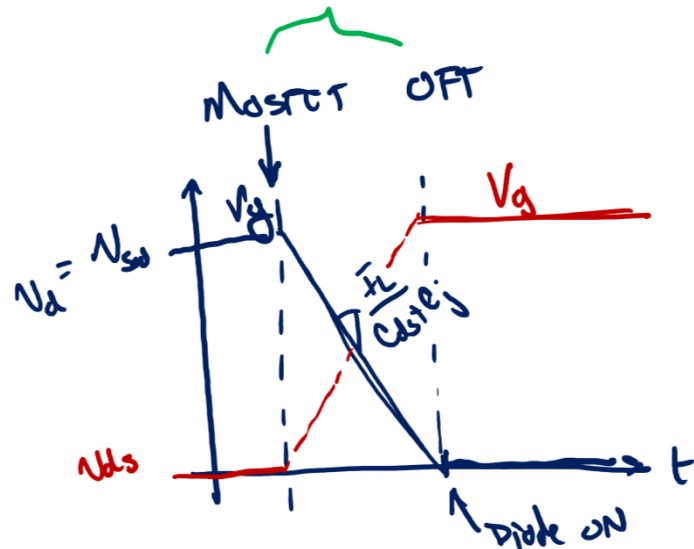
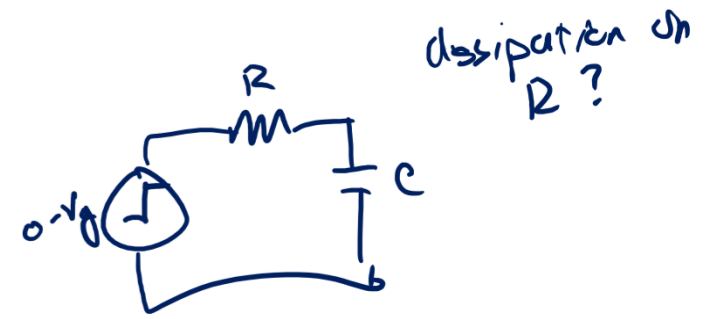
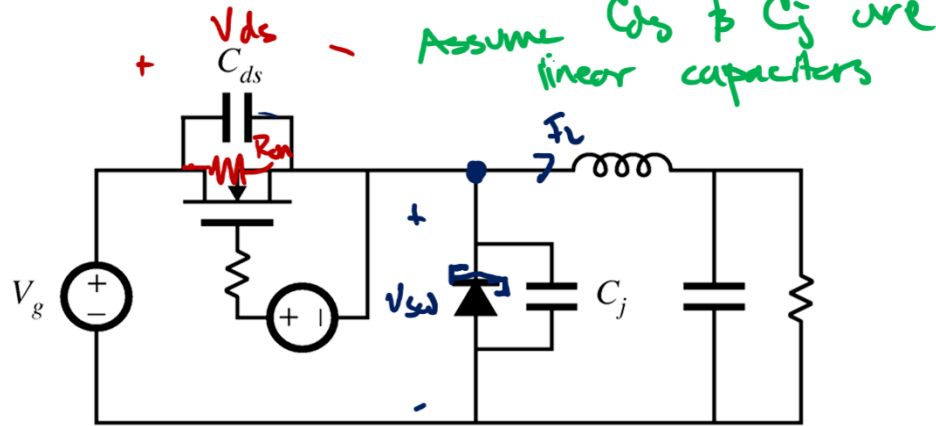
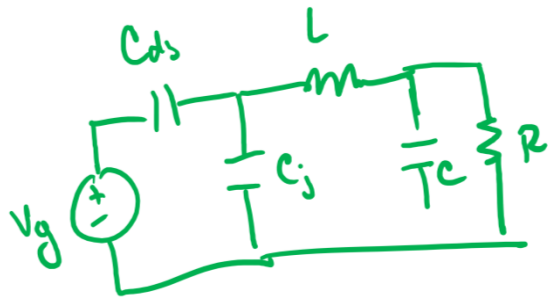
\nearrow design
 \searrow material properties

$$C_{sp} = \frac{C_{ds}(V_{BV})}{A} = \frac{E_{crit}}{2V_{BV}}$$

$$R_{sp} \cdot C_{sp} = R_{on} \cdot C_{ds}(V_{BV}) = \frac{2V_{BV}}{\mu_n E_{crit}^2}$$



Switching Losses: Output Capacitance



$E_{ds} = \frac{1}{2} C_{ds} V_g^2 \rightarrow$ stored in C_{ds}
 $E_j = -\frac{1}{2} C_j V_g^2 \rightarrow$ removed from C_j & supplied back to circuit



$E_{ds} = \frac{1}{2} C_{ds} V_g^2 \rightarrow$ lost in R_{on}
 $E_j = \frac{1}{2} C_j V_g^2 \rightarrow$ lost in R_{on} from resistive charging of C_j

Over the period $P_{swic} = (E_{ds} + E_j) f_s = \frac{1}{2} (C_{ds} + C_j) V_g^2 f_s$